CMOSH-4E

ENHANCED SPECIFICATION
SURFACE MOUNT SILICON SCHOTTKY DIODE

ENHANCED E SPECIFICATION

SOD-523 CASE

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMOSH-4E is an enhanced version of the CMOSH-3 silicon Schottky diode in an SOD-523 surface mount package.

MARKING CODE: 4E

ENHANCED SPECIFICATIONS:

- I_F from 100mA MAX to 200mA MAX
- BV_R from 30V MIN to 40V MIN
- V_F from 1.0V MAX to 0.8V MAX

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
♦ **Peak Repetitive Reverse Voltage**	**V_{RRM}**	**40**	**V**
♦ **Continuous Forward Current**	**I_F**	**200**	**mA**
Peak Repetitive Forward Current	I_{FRM}	350	mA
Peak Forward Surge Current, tp=10ms	I_{FSM}	750	mA
Power Dissipation	P_D	250	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	500	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

	SYMBOL	**TEST CONDITIONS**	**MIN**	**TYP**	**MAX**	**UNITS**
	I_R	V_R=25V		90	500	nA
	I_R	V_R=25V, T_A=100°C		25	100	µA
♦	**BV_R**	**I_R=100µA**	**40**	**50**		**V**
	V_F	I_F=2.0mA		0.29	0.33	V
♦	**V_F**	**I_F=15mA**		**0.37**	**0.42**	**V**
♦	**V_F**	**I_F=100mA**		**0.51**	**0.80**	**V**
♦♦	**V_F**	**I_F=200mA**		**0.65**	**1.0**	**V**
	C_J	V_R=1.0V, f=1.0MHz		7.0		pF
	t_{rr}	I_F=I_R=10mA, I_{rr}=1.0mA, R_L=100Ω			5.0	ns

♦ Enhanced specification.
♦♦ Additional Enhanced specification.

R5 (16-February 2016)

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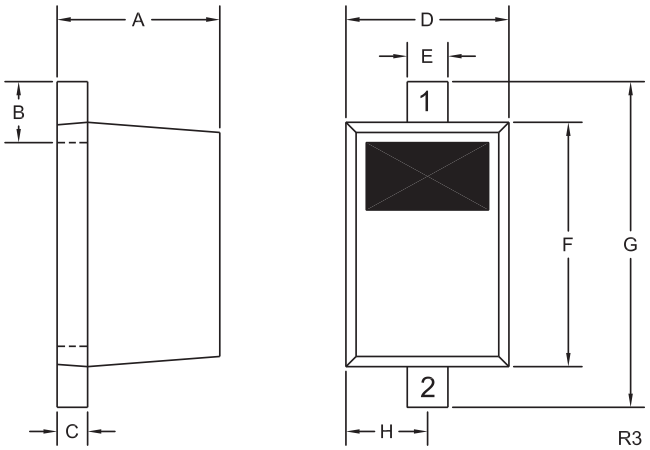
SOD-523 CASE - MECHANICAL OUTLINE



LEAD CODE:
1) Cathode
2) Anode

MARKING CODE: 4E

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.020	0.031	0.50	0.80
B	0.008	0.016	0.20	0.40
C	0.002	0.008	0.05	0.20
D	0.028	0.035	0.70	0.90
E	0.008	0.014	0.20	0.35
F	0.039	0.055	1.00	1.40
G	0.055	0.071	1.40	1.80
H	0.016		0.40	

SOD-523 (REV: R3)

R5 (16-February 2016)

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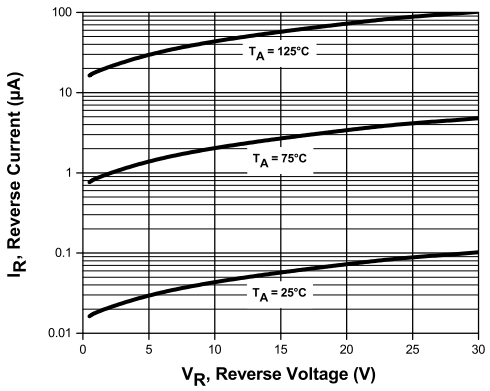
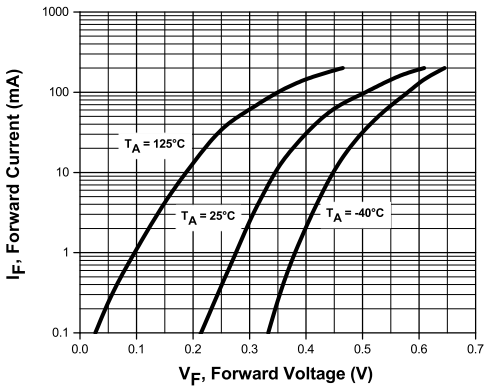
TYPICAL ELECTRICAL CHARACTERISTICS

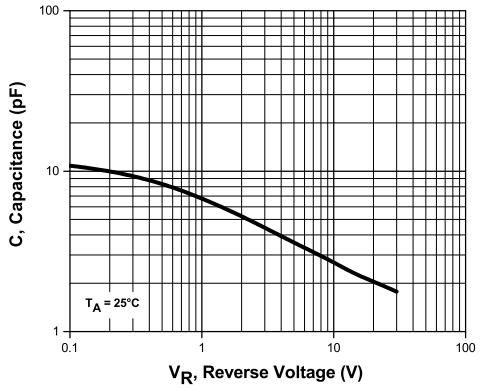
Leakage Current



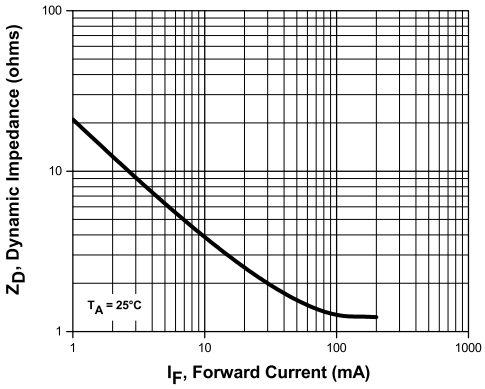
Forward Voltage



Capacitance



Forward Dynamic Impedance



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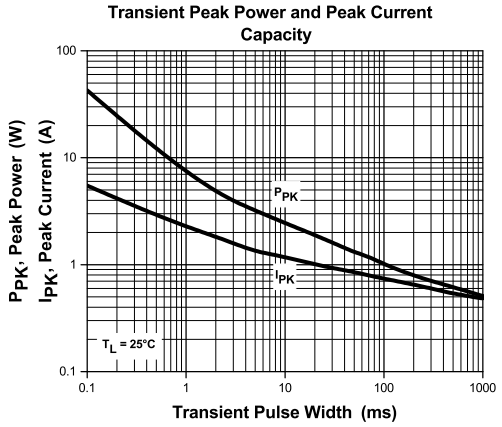
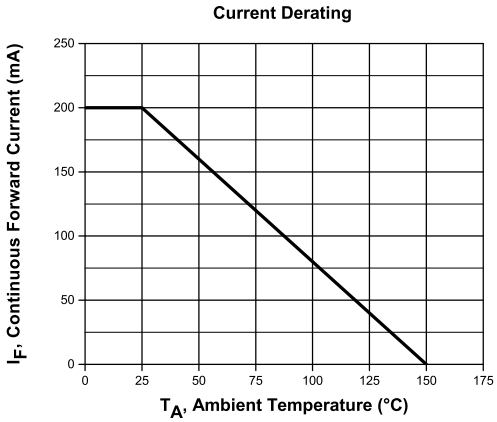
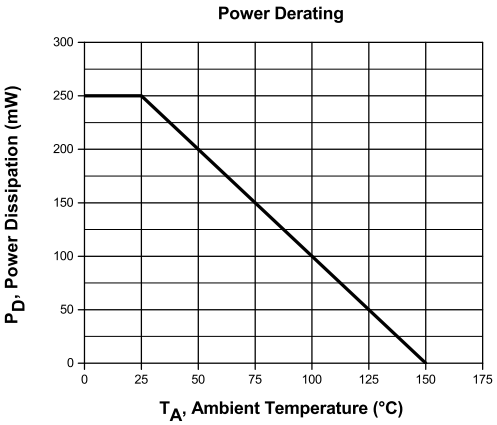
TYPICAL ELECTRICAL CHARACTERISTICS







OUTSTANDING SUPPORT AND SUPERIOR SERVICES

PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

Corporate Headquarters & Customer Support Team

Central Semiconductor Corp.
145 Adams Avenue
Hauppauge, NY 11788 USA
Main Tel: (631) 435-1110
Main Fax: (631) 435-1824
Support Team Fax: (631) 435-3388
www.centralsemi.com

Worldwide Field Representatives:
www.centralsemi.com/wwreps

Worldwide Distributors:
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